

ABSTRACT

The present invention provides a method for manufacturing an SOI wafer with high productivity in which generation of a void is suppressed in manufacturing the SOI wafer. The method for manufacturing an SOI wafer of the present invention comprises the steps of: forming an insulating layer on at least one wafer of two starting wafers; and adhering the one wafer to the other wafer without an adhesive, wherein there is used as the starting wafer a wafer having no line defect on a surface thereof. Also, the method for manufacturing an SOI wafer of the present invention comprises the steps of: forming an insulating layer on at least one wafer of two starting wafers; and adhering the one wafer to the other wafer without an adhesive, wherein the starting wafer is subjected to high temperature heat treatment in advance.